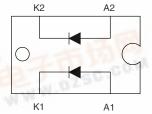


COMPLIANT

## Vishay High Power Products

# HEXFRED® Ultrafast Soft Recovery Diode, 60 A





40 A at 100 °C

**SOT-227** 

I<sub>F(DC)</sub> at T<sub>C</sub>

PRODUCT SUMMARY				
$V_{R}$	600 V			
V <sub>F</sub> (typical) at 125 °C	1.4 V			
Q <sub>rr</sub> (typical)	270 nC			
I <sub>RRM</sub> (typical)	7.0 A			
t <sub>rr</sub> (typical)	65 ns			
dl/dt (typical) at 125 °C	270 A/us			

#### **FEATURES**

- Fast recovery time characteristic
- Electrically isolated base plate
- Large creepage distance between terminal
- Simplified mechanical designs, rapid assembly
- UL pending
- Totally lead (Pb)-free
- · Designed for industrial level

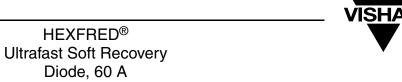
#### **DESCRIPTION**

This SOT-227 modules with HEXFRED® rectifier are available in two basic configurations. They are the antiparallel and the parallel configurations. The antiparallel configuration (HFA120EA60) is used for simple series rectifier and high voltage application. The parallel configuration (HFA120FA60) is used for simple parallel rectifier and high current application. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built. These modules are intended for general applications such as power supplies, battery chargers, electronic welders, motor control, DC chopper, and inverters.

ABSOLUTE MAXIMUM RATINGS PER LEG				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V <sub>R</sub>	60 (C) -	600	V
Continuous forward current	C.CPM	T <sub>C</sub> = 25 °C	75	
		T <sub>C</sub> = 100 °C	40	A
Single pulse forward current	I <sub>FSM</sub>		TBD	A
Maximum repetitive forward current	I <sub>FRM</sub>		180	
RMS isolation voltage, any terminal to case	V <sub>ISOL</sub>	t = 1 minute	2500	V
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	180	w
		T <sub>C</sub> = 100 °C	71 71	5C-0-W
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>	- LT- 12	- 55 to 150	°C

ELECTRICAL SPECIFICATIONS PER LEG (T <sub>,I</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA		600	-	-	
Maximum forward voltage V <sub>FM</sub>		I <sub>F</sub> = 60 A	See fig. 1	-	1.5	1.7	V
	$V_{FM}$	I <sub>F</sub> = 120 A		-	1.9	2.1	
	I <sub>F</sub> = 60 A, T <sub>J</sub> = 125 °C		-	1.4	1.6		
Maximum reverse leakage current I <sub>RM</sub>	$V_R = V_R$ rated	Coo fig. 0	-	2.5	20		
	IRM	$T_J = 125 ^{\circ}\text{C},  V_R = 0.8 ^{\circ}\text{x} ^{\circ}\text{V}_R ^{\circ}\text{rated}$	See fig. 2	-	130	2000	μΑ
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	-	120	170	pF

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<b>DYNAMIC RECOVERY CHARACTERISTICS PER LEG</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	34	-	
Reverse recovery time See fig. 5, 6 and 16	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	65	98	ns
300 lig. 0, 0 and 10	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	130	200	
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C	$I_F = 60 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	7.0	13	Α
See fig. 7 and 8	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	13	23	_ ^
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	270	410	nC
See fig. 9 and 10	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	490	740	IIC
Peak rate of recovery current during $t_b$ See fig. 11 and 12	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	350	-	A /
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		=	270	-	A/μs

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	
Junction to case, single leg conducting	В	-	-	0.70		
Junction to case, both legs conducting	- R <sub>thJC</sub>	-	-	0.35	°C/W K/W	
Case to sink, flat, greased surface	R <sub>thCS</sub>	-	0.05	-		
Weight		-	30	-	g	
Mounting torque		-	1.3	-	Nm	



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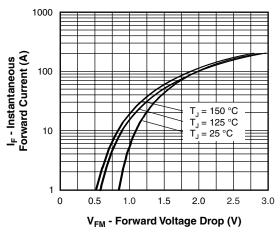


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

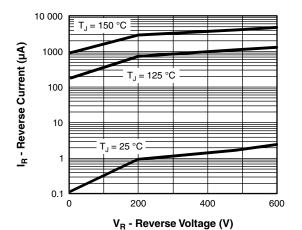


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

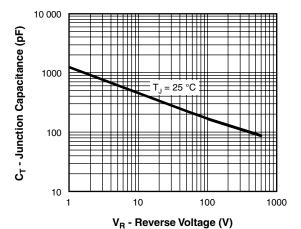


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

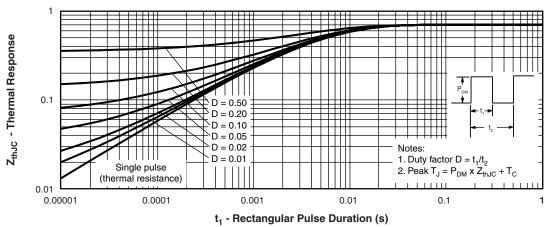


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (Per Leg)

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## HEXFRED® Ultrafast Soft Recovery Diode, 60 A



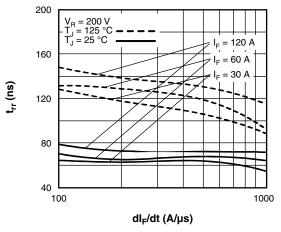


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt (Per Leg)

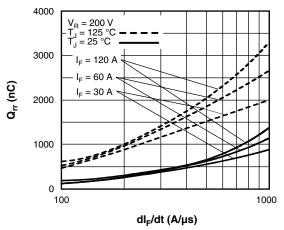


Fig. 7- Typical Stored Charge vs. dl<sub>F</sub>/dt (Per Leg)

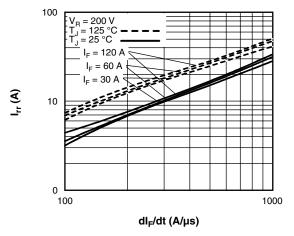


Fig. 6 - Typical Recovery Current vs. dI<sub>F</sub>/dt (Per Leg)

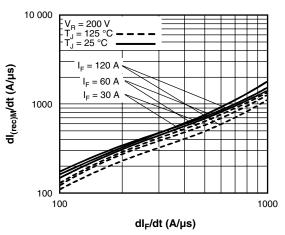


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$  (Per Leg)



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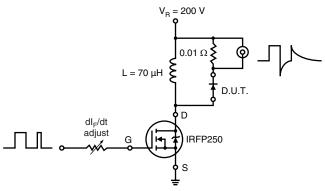
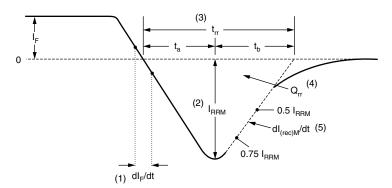


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- $\begin{array}{l} \text{(3) } \textbf{t}_{\text{rr}} \text{ reverse recovery time measured} \\ \text{from zero crossing point of negative} \\ \text{going I}_{\text{F}} \text{ to point where a line passing} \\ \text{through 0.75 I}_{\text{RRM}} \text{ and 0.50 I}_{\text{RRM}} \\ \text{extrapolated to zero current.} \end{array}$
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions

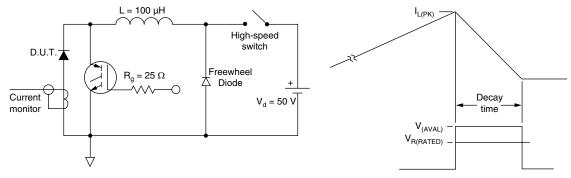


Fig. 11 - Avalanche Test Circuit and Waveforms

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HEXFRED® Ultrafast Soft Recovery Diode, 60 A



#### **ORDERING INFORMATION TABLE**

1 - HEXFRED® family

Process: A electron irradiated

**3** - Current rating (120 = 120 A)

- Package indicator (SOT-227)

5 - Voltage rating (60 = 600 V)

P = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95036				
Packaging information	http://www.vishay.com/doc?95037			

www.vishay.com

For technical questions, contact: ind-modules@vishay.com

Document Number: 94049



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